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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>		<b>Complete if Known</b>			
		Application Number	09/921,518		
		Filing Date	August 1, 2001		
		First Named Inventor	John T. Moore		
		Art Unit	2818		
		Examiner Name	Phuc T. Dang		
Sheet	1	of	8	Attorney Docket Number	M4065.0696/P696

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
P D	AA	5,761,115	06/02/1998	Kozicki et al.	
↑	AB	6,084,796	07/04/2000	Kozicki et al.	
	AC	5,914,893	06/22/1999	Kozicki et al.	
	AD	5,896,312	04/20/1999	Kozicki et al.	
↓	AE	6,388,324	05/14/2002	Kozicki et al.	
	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
P D	AG	5,500,532	03/19/1996	Kozicki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>4</sup> -Number <sup>5</sup> -Kind Code <sup>6</sup> (if known)				
P R	BA	WO 02/21542	03/14/2002	Kozicki et al.		
↓	BB	WO 00/48196	08/17/2000	Kozicki et al.		
	BC	WO 97/48032	12/18/1997	Kozicki et al.		
P D	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	PHUC T. DANG	Date Considered	12/4/03
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Sheet	2	8	Attorney Docket Number	M4065.0696/P696

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
PD	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
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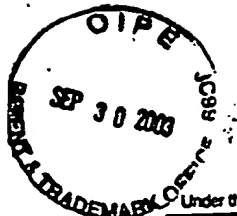
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P.D.		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CX	Boalchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
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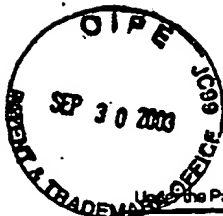
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PD		silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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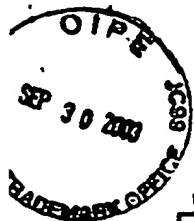
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Sheet 6	8	Attorney Docket Number	M4065.0696/P696

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	09/921,518
		Filing Date	August 1, 2001
		First Named Inventor	John T. Moore
		Group Art Unit	2818
		Examiner Name	Phuc T. Dang
Sheet 7	8	Attorney Docket Number	M4065.0696/P696

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		First Named Inventor	John T. Moore		
		Group Art Unit	2818		
		Examiner Name	Phuc T. Dang		
Sheet	8		8	Attorney Docket Number	M4065.0696/P696

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Examiner Signature	PHUC T. DANG	Date Considered	12/4/03
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